Diego Calvo Ruiz

List of Publications by Year in descending order

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1937685 1720034 11 51 4 7 citations h-index g-index papers 11 11 11 46 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	High-Speed Steep-Slope GalnAs Impact Ionization MOSFETs (I-MOS) With ⟨i>SS⟨ i> = 1.25 mV/decâ€"Part II: Dynamic Switching and RF Performance. IEEE Transactions on Electron Devices, 2022, 69, 3549-3556.	3.0	3
2	High-Speed Steep-Slope GalnAs Impact Ionization MOSFETs (I-MOS) With SS = 1.25 mV/dec—Part I: Material and Device Characterization, DC Performance, and Simulation. IEEE Transactions on Electron Devices, 2022, 69, 3542-3548.	3.0	2
3	Impact of Reduced Gateâ€toâ€Source Spacing on Indium Phosphide High Electron Mobility Transistor Performance. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000191.	1.8	2
4	Low-Noise Microwave Performance of 30 nm GalnAs MOS-HEMTs: Comparison to Low-Noise HEMTs. IEEE Electron Device Letters, 2020, 41, 1320-1323.	3.9	6
5	InAs Channel Inset Effects on the DC, RF, and Noise Properties of InP pHEMTs. IEEE Transactions on Electron Devices, 2019, 66, 4685-4691.	3.0	10
6	New GalnAs/InAs/InP Composite Channels for mm-Wave Low-Noise InP HEMTs., 2019, , .		1
7	Impact Ionization Control in 50 nm Low-Noise High-Speed InP HEMTs with InAs Channel Insets. , 2019, , .		8
8	Effects of Electrochemical Etching on InP HEMT Fabrication. IEEE Transactions on Semiconductor Manufacturing, 2019, 32, 496-501.	1.7	6
9	Evaluation of energy barriers for topological transitions of Si self-interstitial clusters by classical molecular dynamics and the kinetic activation-relaxation technique. , 2017, , .		0
10	Pt Gate Sink-In Process Details Impact on InP HEMT DC and RF Performance. IEEE Transactions on Semiconductor Manufacturing, 2017, 30, 462-467.	1.7	13
11	Novel Vitrified-Bond Ultra-Fine Grinding Technology for SiC Polishing. Materials Science Forum, 0, 1062, 155-159.	0.3	0